

Silicon PNP Power Transistors

2SA957 2SA958

DESCRIPTION

- With TO-220 package
- High breakdown voltage
- High power dissipation

APPLICATIONS

- For general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

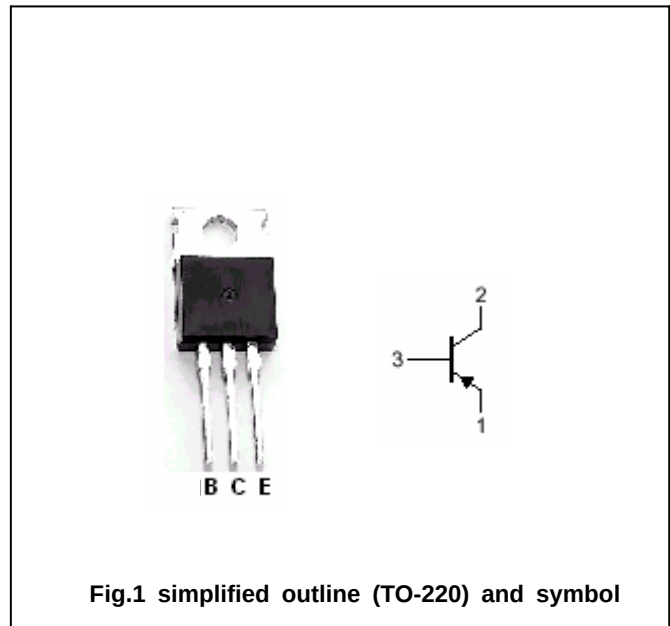


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA957	Open emitter	-150	V
		2SA958		-200	
V_{CEO}	Collector-emitter voltage	2SA957	Open base	-150	V
		2SA958		-200	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2.0	A
I_B	Base current			-1.0	A
P_T	Total power dissipation		$T_C=25^{\circ}\text{C}$	30	W
T_j	Junction temperature			150	$^{\circ}\text{C}$
T_{stg}	Storage temperature			-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(BR)}$	Collector-emitter breakdown voltage	2SA957	$I_C=-25mA, I_B=0$	-150			V
		2SA958		-200			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=-0.7A; I_B=-0.07A$			-1.5	V
I_{CBO}	Collector cut-off current	2SA957	$V_{CB}=-150V; I_E=0$			-100	μA
		2SA958	$V_{CB}=-200V; I_E=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=-6V; I_C=0$			-1.0	mA
h_{FE}	DC current gain		$I_C=-0.7A; V_{CE}=-10V$	40			
f_T	Transition frequency		$I_C=-0.2A; V_{CE}=-12V$		20		MHz

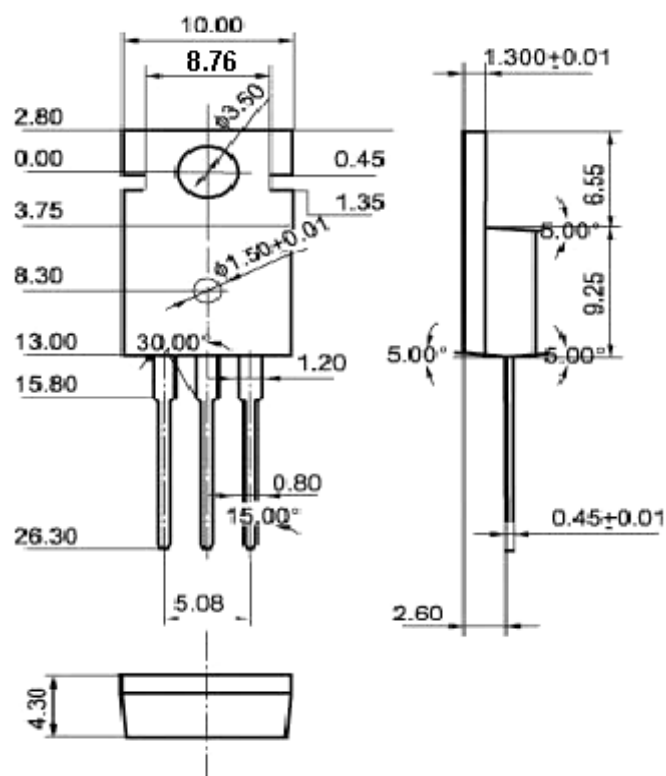
Switching times resistive load

t_r	Rise time	$I_C=-1.0A, I_{B1}=-I_{B2}=-0.1A$ $R_L=20\Omega; V_{CC}=-20V$		0.4		μs
t_s	Storage time			1.5		μs
t_f	Fall time			0.5		μs

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)